

MSKSEMI 美森科

SEMICONDUCTOR



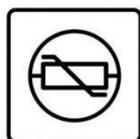
ESD



TVS



TSS



MOV



GDT



PLED

MEL357X

产品手册

描述

MEL357X 是一块小外形的贴片光电耦合器件, 适合表面贴装生产。MEL357X 是由一个砷化镓发光二极管和一个光电晶体管组成的光电耦合器, 它的体积比 DIP 小, 适用于高密度表面贴装应用, 如可编程控制器等。

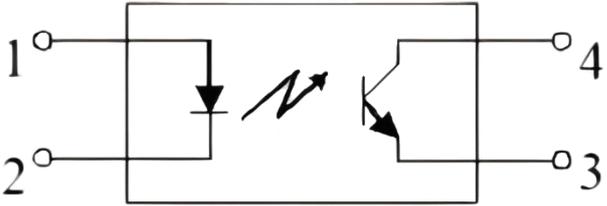
特性

- 电流转换比 (CTR) 范围: 50~600% ($I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
- 输入-输出隔离电压 ($V_{iso} = 3750\text{ Vrms}$)
- 集电极-发射极击穿电压 $BV_{CEO} \geq 80\text{V}$

应用领域

- 开关电源, 智能电表
- 工业控制, 测量仪器
- 办公设备, 比如复印机
- 家用电器, 比如空调、风扇、热水器等

封装信息及内部引脚配置

封装	引脚配置
	
SOP-4	

订单信息

型号	封装	最小包装
MEL357X	SOP-4	3000

极限参数 (Ta=25°C)

参数		符号	额定值	单位
输入	正向电流	I_F	50	mA
	正向脉冲电流	I_{FP}	1	A
	反向电压	V_R	6	V
	功耗	P	70	mW
	结温	T_j	125	°C
输出	集电极功耗	P_C	150	mW
	集电极电流	I_C	50	mA
	集电极-发射极电压	V_{CE0}	80	V
	发射极-集电极电压	V_{ECO}	7	V
	结温	T_j	125	°C
总功耗		P_{tot}	200	mW
隔离电压		V_{iso}	3750	V_{rms}
工作温度		T_{opr}	-55~+110	°C
储存温度		T_{stg}	-55~+125	°C
焊接温度		T_{sol}	260	°C

CTR 分级表

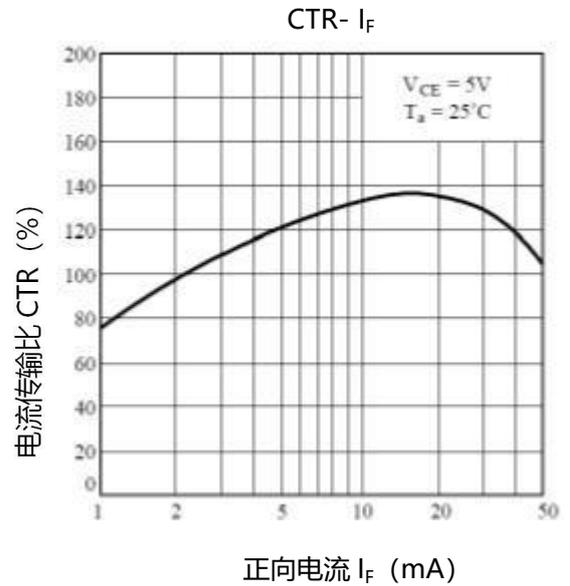
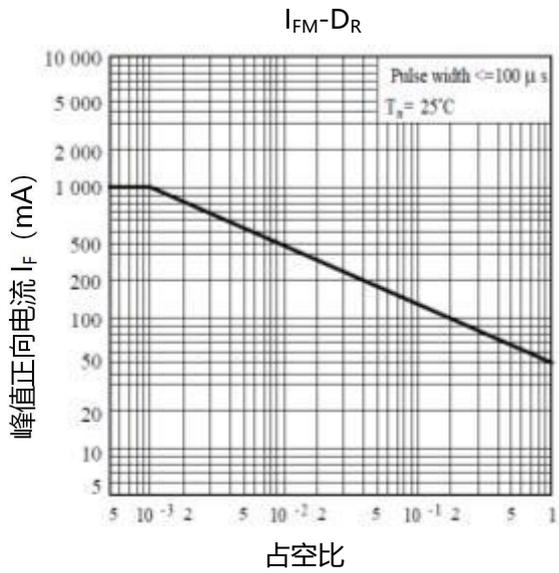
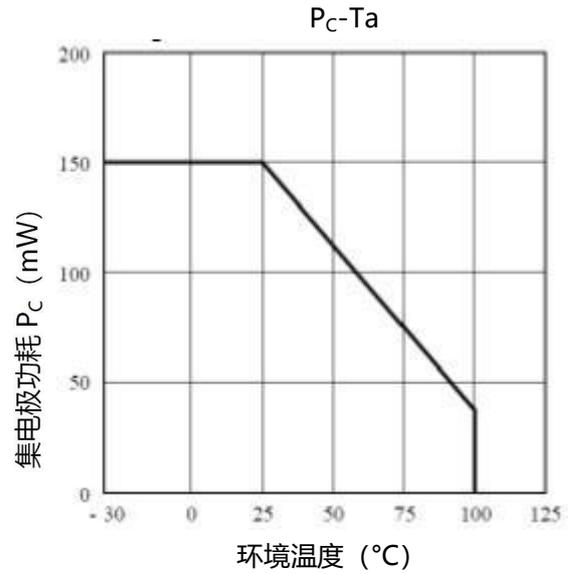
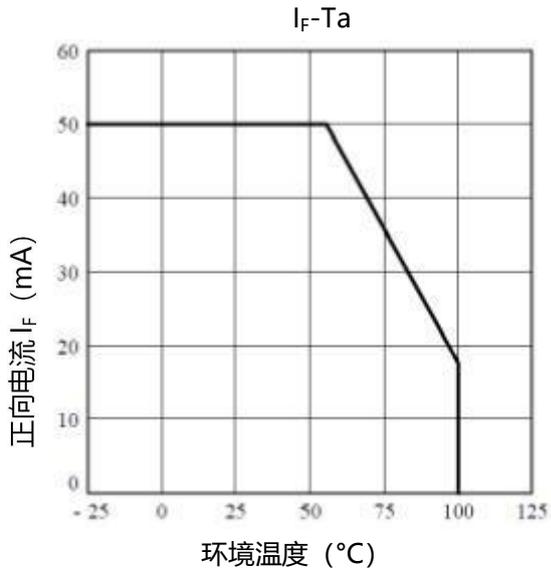
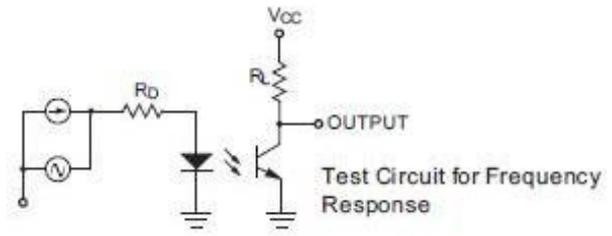
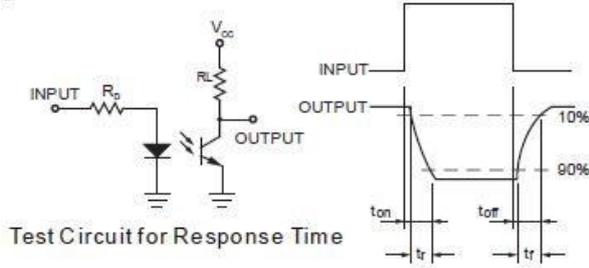
型号	管体标记	分级标准	I_C (mA)		对应CTR (%)	
			$I_F = 5mA, V_{CE} = 5V, T_a = 25^\circ C$		$I_F = 5mA, V_{CE} = 5V, T_a = 25^\circ C$	
			Min	Max	Min	Max
MEL357		Blank	2.5	30.0	50	600
MEL357A		A	4.0	8.0	80	160
MEL357B		B	6.5	13.0	130	260
MEL357C		C	10.0	20.0	200	400
MEL357D		D	15.0	30.0	300	600

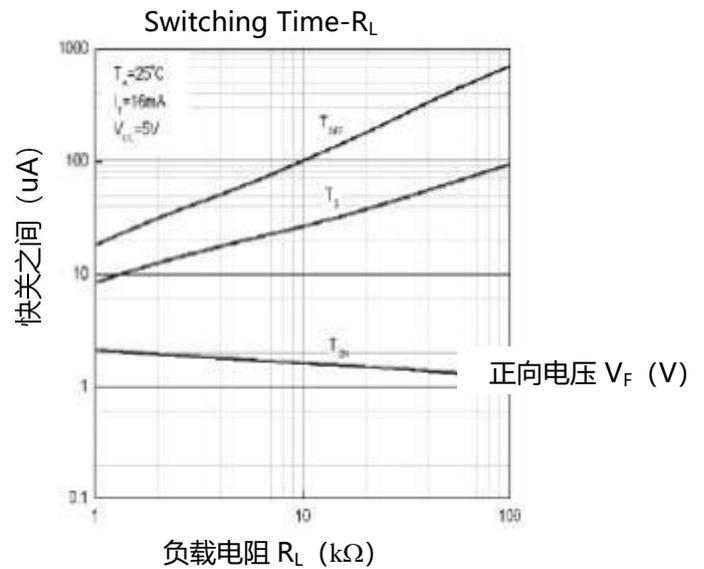
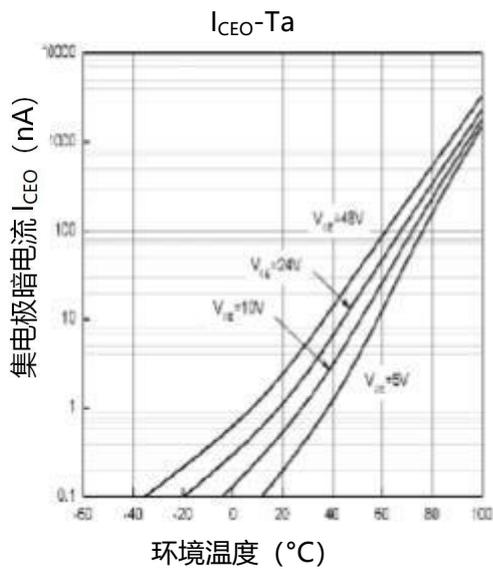
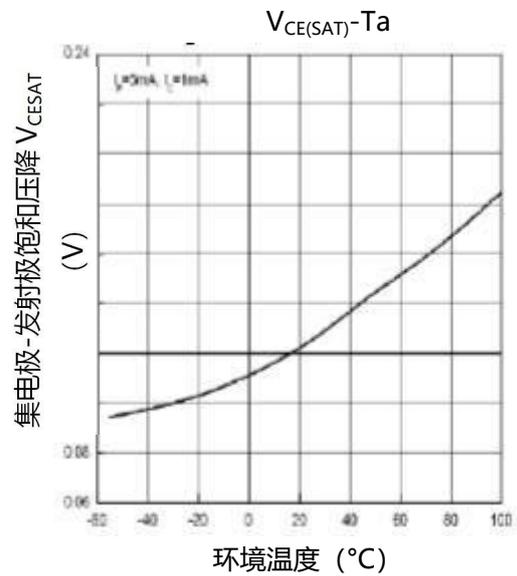
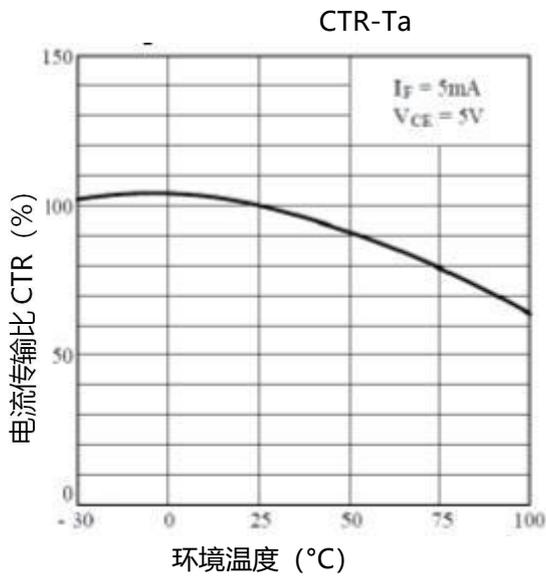
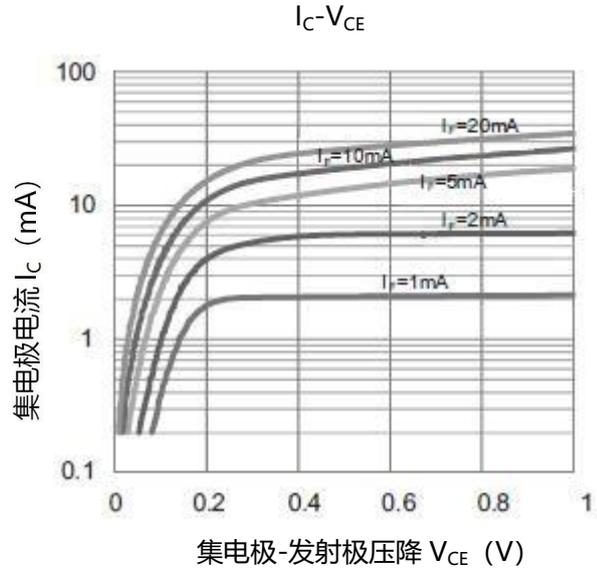
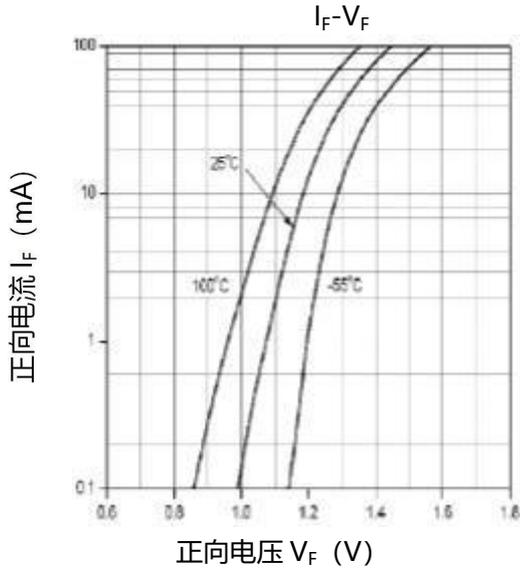
光电特性 (Ta=25°C)

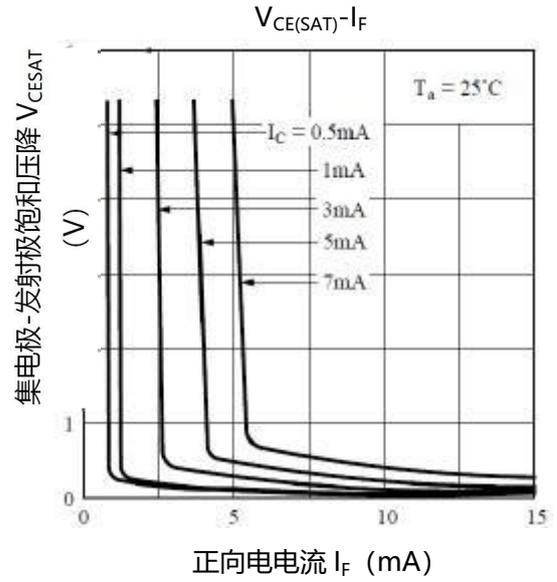
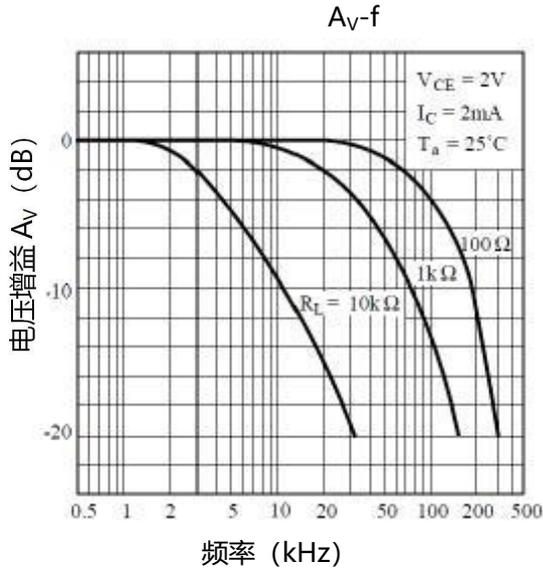
Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
输入	正向电压	V_F	$I_F=20\text{mA}$		1.2	1.4	V
	反向电流	I_R	$V_R=5\text{V}$	-	-	10	μA
	终端电容	C_t	$V=0, f=1\text{kHz}$	-	30	250	pF
输出	集电极暗电流	I_{CEO}	$V_{CE}=70\text{V}$	-	-	100	nA
	集电极-发射极击穿电压	BV_{CEO}	$I_C=0.1\text{mA}, I_F=0$	80	-	-	V
	发射极-集电极击穿电压	BV_{ECO}	$I_E=0.1\text{mA}, I_F=0$	7	-	-	V
传输特性	电流转换比	CTR	$I_F=5\text{mA}, V_{CE}=5\text{V}$	50	-	400	%
	集电极-发射极饱和压降	$V_{CE(sat)}$	$I_F=20\text{mA}, I_C=1\text{mA}$	-	0.1	0.2	V
	隔离电阻	R_{ISO}	DC1000V, 40~60%R.H.	1×10^{11}	-	-	Ω
	隔离电容	C_f	$V=0, f=1\text{MHz}$	-	0.6	1.0	pF
	集电极-发射极电容	C_{CE}	$V=0, f=1\text{MHz}$		10		pF
	截止频率	F_c	$V_{CE}=5\text{V}, I_C=2\text{mA},$ $R_L=100\Omega, -3\text{dB}$	-	80	-	kHz
开关时间	上升时间	T_r	$V_{CE}=10\text{V}, I_C=2\text{mA},$ $R_L=100\Omega$	-	4	18	μs
	下降时间	T_f		-	3	18	μs

 * $CTR=I_C/I_F \times 100\%$

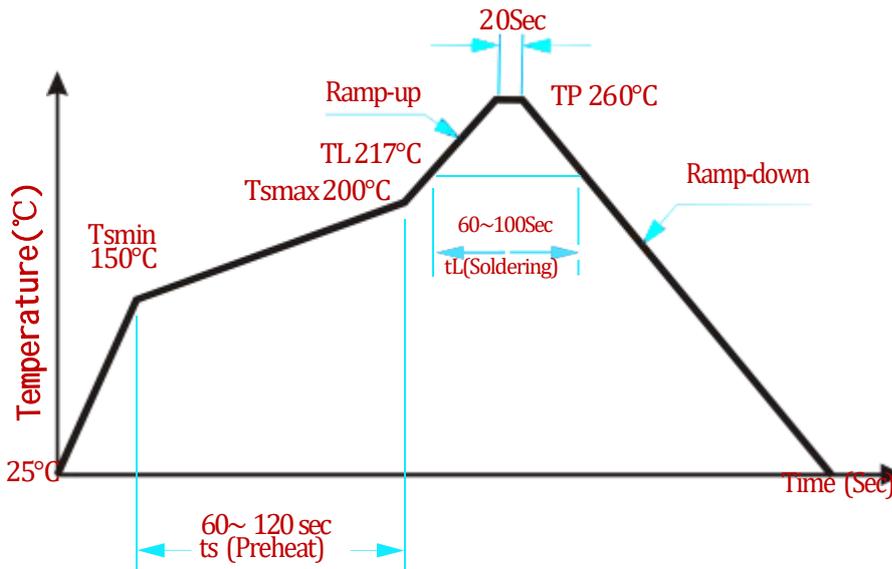
测试电路



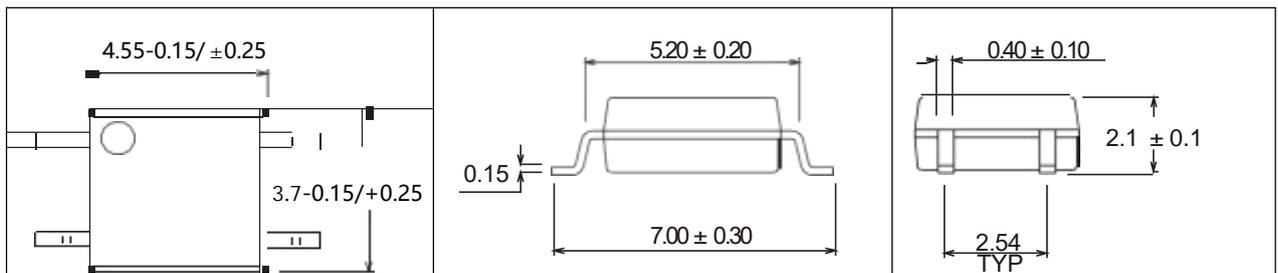




回流焊温度曲线图



外形尺寸



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